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PATENT

Attorney Docket No.: 5308-389

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Saxler

Confirmation No.: 8522

Application No.: 10/772,882

Group Art Unit: 2815

Filed: February 5, 2004

Examiner Name: Jerome Jackson, Jr.

For: **NITRIDE HETEROJUNCTION TRANSISTORS HAVING CHARGE-TRANSFER
INDUCED ENERGY BARRIERS AND METHODS OF FABRICATING THE
SAME**

Date: June 14, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office to 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004. Also enclosed is a translation or a concise explanation of each non-English language document enclosed. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Therefore, no fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,



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CERTIFICATE OF MAILING UNDER 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on June 14, 2005.



Erin A. Cambron

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| Substitute form 1449A/PTO | | Complete if Known | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary) | | Application Number | 10/772,882 |
| | | Filing Date | February 5, 2004 |
| | | First Named Inventor | Saxler |
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| Sheet | 1 | of | 3 |

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